1. General description

NPN/NPN general-purpose double transistor in a very small SOT363 (SC-88) Surface-Mounted Device (SMD) plastic package.

PNP/PNP complement: BC857BSH-Q NPN/PNP complement: BC847BPNH-Q

2. Features and benefits

- Low collector capacitance
- Low collector-emitter saturation voltage
- · Closely matched current gain
- · Reduces number of components and board space
- No mutual interference between the transistors
- High-temperature applications up to 175 °C
- Qualified according to AEC-Q101 and recommended for use in automotive applications

3. Applications

· General-purpose switching and amplification

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit	
Per transistor	Per transistor							
V _{CEO}	collector-emitter voltage	open base		-	-	45	V	
I _C	collector current			-	-	100	mA	
h _{FE}	DC current gain	$V_{CE} = 5 \text{ V}; I_{C} = 2 \text{ mA}; T_{amb} = 25 ^{\circ}\text{C}$		200	300	450		



5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	E1	emitter TR1	□6 □5 □4	C1 B2 E2
2	B1	base TR1		
3	C2	collector TR2		(TR1) TR2)
4	E2	emitter TR2	H ₁ H ₂ H ₃	
5	B2	base TR2	TSSOP6 (SOT363)	I I I E1 B1 C2
6	C1	collector TR1		sym140

6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BC847BSH-Q		plastic, surface-mounted package; 6 leads; 0.65 mm pitch; 2.1 mm x 1.25 mm x 0.95 mm body	SOT363

7. Marking

Table 4. Marking codes

Type number	Marking code[1]
BC847BSH-Q	7C%

^{[1] % =} placeholder for manufacturing site code

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

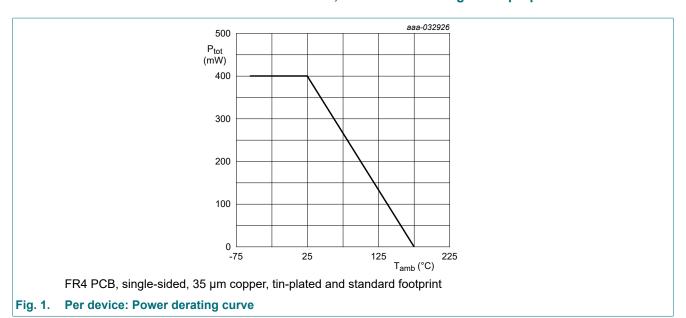
Symbol	Parameter	Conditions		Min	Max	Unit
Per transisto	or		'			
V _{CBO}	collector-base voltage	open emitter		-	50	V
V _{CEO}	collector-emitter voltage	open base		-	45	V
V _{EBO}	emitter-base voltage	open collector		-	7	V
I _C	collector current			-	100	mA
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms		-	200	mA
I _{BM}	peak base current			-	200	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1]	-	270	mW
Per device			,			
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1]	-	400	mW
Tj	junction temperature			-	175	°C
T _{amb}	ambient temperature			-55	175	°C
T _{stg}	storage temperature			-65	175	°C

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided, 35 µm copper, tin-plated and standard footprint.

BC847BSH-Q

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45 V, 100 mA NPN/NPN general-purpose double transistor



9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions			Min	Тур	Max	Unit
Per transist	tor							
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1	1]	-	-	556	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point				-	-	170	K/W
Per device			'				'	
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1	1]	-	-	375	K/W

[1] Device mounted on an FR4 PCB, single-sided, 35 µm copper, tin-plated and standard footprint.

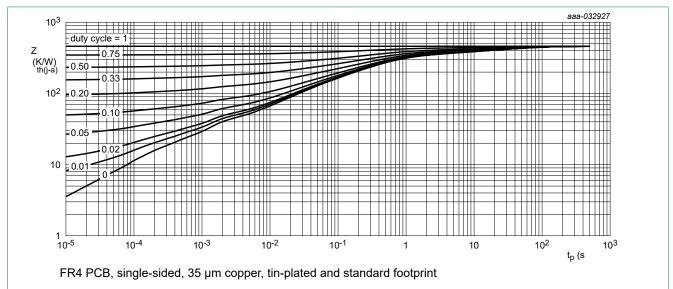


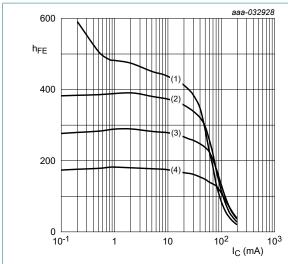
Fig. 2. Per transistor: Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per transist	or						
V _{(BR)CBO}	collector-base breakdown voltage	$I_C = 100 \ \mu A; I_E = 0 \ A; T_{amb} = 25 \ ^{\circ}C$		50	-	-	V
V _{(BR)CEO}	collector-emitter breakdown voltage	$I_C = 2 \text{ mA}; I_B = 0 \text{ A}; T_{amb} = 25 ^{\circ}\text{C}$		45	-	-	V
$V_{(BR)EBO}$	emitter-base breakdown voltage	$I_C = 0 \text{ A}; I_E = 100 \mu\text{A}; T_{amb} = 25 \text{ °C}$		7	-	-	V
I _{CBO}	collector-base cut-off	V _{CB} = 30 V; I _E = 0 A; T _{amb} = 25 °C		-	-	15	nA
	current	$V_{CB} = 30 \text{ V}; I_E = 0 \text{ A}; T_j = 150 ^{\circ}\text{C}$		-	-	5	μA
I _{EBO}	emitter-base cut-off current	V _{EB} = 7 V; I _C = 0 A; T _{amb} = 25 °C		-	-	100	nA
h _{FE}	DC current gain	V _{CE} = 5 V; I _C = 2 mA; T _{amb} = 25 °C		200	300	450	
V _{CEsat}	collector-emitter	I_C = 10 mA; I_B = 0.5 mA; T_{amb} = 25 °C		-	50	100	mV
	saturation voltage	I_C = 100 mA; I_B = 5 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C		-	200	300	mV
22001	base-emitter saturation	I_C = 10 mA; I_B = 0.5 mA; T_{amb} = 25 °C	[1]	-	750	850	mV
	voltage	I _C = 100 mA; I _B = 5 mA; T _{amb} = 25 °C		-	875	-	mV
V_{BE}	base-emitter voltage	V _{CE} = 5 V; I _C = 2 mA; T _{amb} = 25 °C	[2]	600	655	700	mV
		V _{CE} = 5 V; I _C = 10 mA; T _{amb} = 25 °C	[2]	-	705	770	mV
C _c	collector capacitance	V_{CB} = 10 V; I_{E} = 0 A; i_{e} = 0 A; f = 1 MHz; T_{amb} = 25 °C		-	1.2	-	pF
C _e	emitter capacitance	$V_{EB} = 0.5 \text{ V}; I_{C} = 0 \text{ A}; i_{c} = 0 \text{ A};$ f = 1 MHz; $T_{amb} = 25 \text{ °C}$		-	11	-	pF
f _T	transition frequency	$V_{CE} = 5 \text{ V}; I_{C} = 10 \text{ mA}; f = 100 \text{ MHz};$ $T_{amb} = 25 \text{ °C}$		100	-	-	MHz
NF	noise figure	V_{CE} = 5 V; I_{C} = 0.2 mA; R_{S} = 2 k Ω ; f = 10 Hz to 15.7 kHz; T_{amb} = 25 °C		-	1.7	-	dB
		V_{CE} = 5 V; I_{C} = 0.2 mA; R_{S} = 2 k Ω ; f = 1 kHz; B = 200 Hz; T_{amb} = 25 °C		-	3.1	-	dB

 $V_{BEsat} \ decreases \ by \ about \ 1.7 \ mV/K \ with \ increasing \ temperature.$ $V_{BE} \ decreases \ by \ about \ 2 \ mV/K \ with \ increasing \ temperature.$

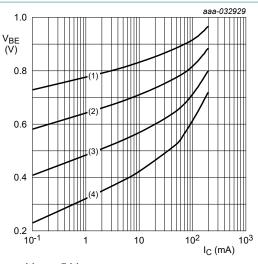


 $V_{CE} = 5 V$ (1) $T_{amb} = 175 °C$

(2) $T_{amb} = 150 \, ^{\circ}C$

(3) $T_{amb} = 25 ^{\circ}C$ (4) $T_{amb} = -40 ^{\circ}C$

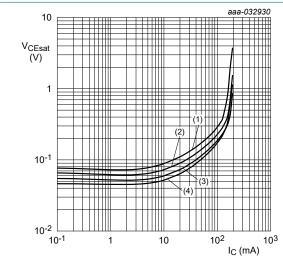
DC current gain as a function of collector Fig. 3. current; typical values



V_{CE} = 5 V (1) T_{amb} = -40 °C (2) T_{amb} = 25 °C

(3) T_{amb} = 100 °C (4) T_{amb} = 175°C

Base-emitter voltage as a function of collector Fig. 4. current; typical values



 $I_C/I_B = 20$

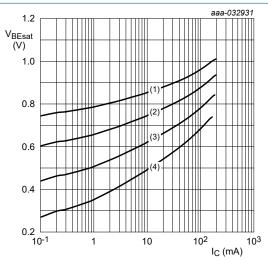
 $(1) T_{amb} = 175 °C$

(2) T_{amb} = 100 °C

(3) $T_{amb} = 25 \, ^{\circ}C$

(4) $T_{amb} = -40 \, ^{\circ}C$

Fig. 5. Collector-emitter saturation voltage as a function of collector current; typical values



 $I_C/I_B = 20$

(1) T_{amb} = -40 °C

(2) $T_{amb} = 25 \, ^{\circ}C$

(3) $T_{amb} = 100 \, ^{\circ}C$

(4) $T_{amb} = 175 \, ^{\circ}C$

Fig. 6. Base-emitter saturation voltage as a function of collector current; typical values

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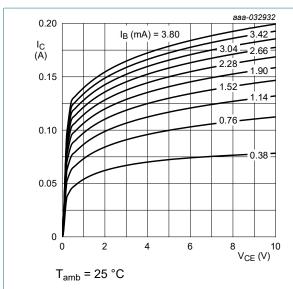


Fig. 7. Collector current as a function of collectoremitter voltage; typical values

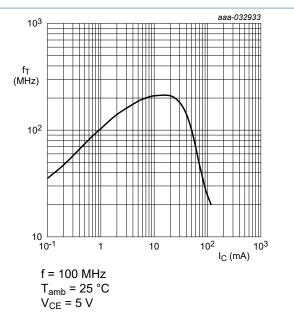


Fig. 8. Transition frequency as a function of collector current; typical values

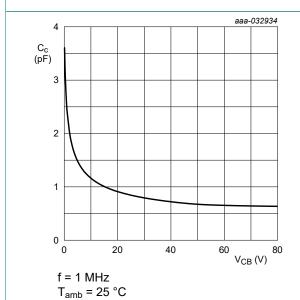
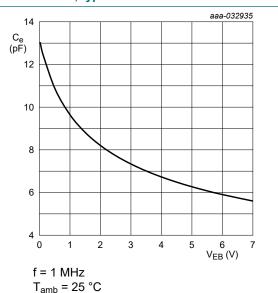


Fig. 9. base voltage; typical values



Collector capacitance as a function of collector- Fig. 10. Emitter capacitance as a function of emitterbase voltage; typical values

11. Test information

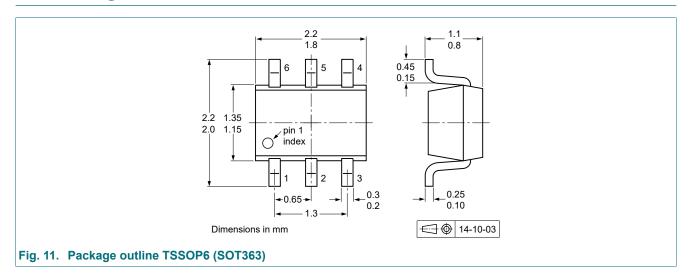
Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

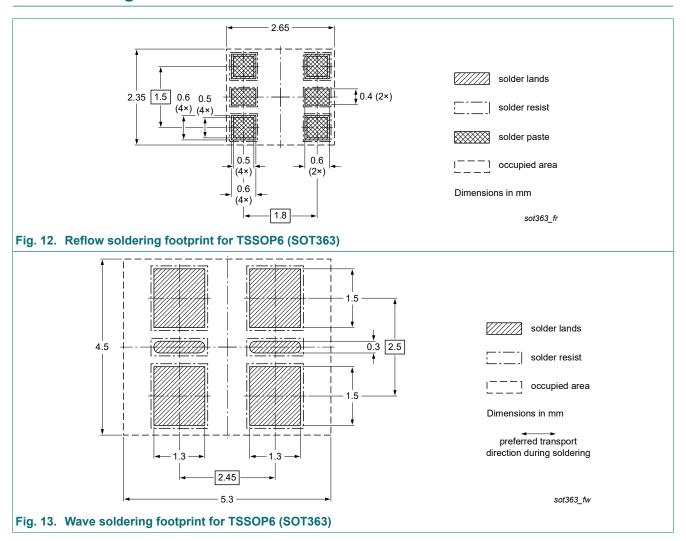
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12. Package outline



13. Soldering



45 V, 100 mA NPN/NPN general-purpose double transistor

14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
BC847BSH-Q v.1	20210506	Product data sheet	-	-

15. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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